## NSN 5962-01-196-6113

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View Online at https://aerobasegroup.com/nsn/5962-01-196-6113

Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Maximum Power Dissipation Rating:
1.04 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and monolithic and bipolar and programmable
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
14 input
Case Outline Source And Designator:
D-3 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes output
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.0 volts power source
Time Rating Per Chacteristic:
45.00 nanoseconds propagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Test Data Document:
14933-82008 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)

24 printed circuit

**Terminal Type And Quantity:** 

Shelf Life:

N/a

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Demilitarization:

No

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